

SBR30A50CT SBR30A50CTF SBR30A50CTI SBR30A50CTB

Super Barrier Rectifier ™

Using state-of-the-art SBR IC process technology, the following features are made possible in a single device:

Major ratings and characteristics

Characteristics	Values	Units
I _{F(AV)} Rectangular Waveform	30	Α
V_{RRM}	50	V
V _F @15A, Tj=125 ^O C	0.44	V, typ
Tj (operating/storage)	-65 to 150	°C

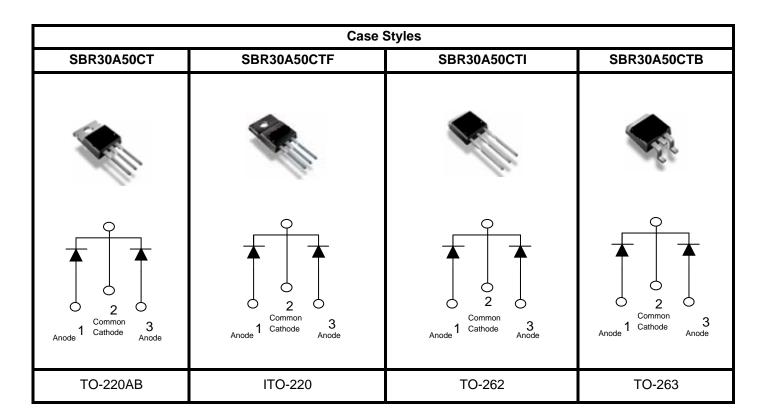
Device optimized for low forward voltage drop to maximize efficiency in Power Supply applications

ELECTRICAL:

- * Low Forward Voltage Drop
- * Reliable High Temperature Operation
- * Super Barrier Design
- * Softest, fast switching capability
- * 150°C Operating Junction Temperature

MECHANICAL:

* Molded Plastic TO-220AB, TO-262, TO-263, and ITO-220 packages





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	SYMBOL			UNITS
DC Blocking Voltage Working Peak Reverse Voltage Peak Repetitive Reverse Voltage	V _{RM} V _{RWM} V _{RRM}	50		Volts
Average Rectified Forward Current (Rated V _R -20Khz Square Wave) - 50% duty cycle	Io	30		Amps
Peak Forward Surge Current - 1/2 60hz	I _{FSM}	250		Amps
Peak Repetitive Reverse Surge Current (2uS-1Khz)	I _{RRM}	3		Amps
Instantaneous Forward Voltage (per leg) $I_F = 15A$; $T_J = 25^{\circ}C$ $I_F = 30A$; $T_J = 25^{\circ}C$ $I_F = 15A$; $T_J = 125^{\circ}C$	V _F	Тур 	Max 0.55 0.69 0.47	Volts
Maximum Instantaneous Reverse Current at Rated V_{RM} $T_J = 25^{\circ}C$ $T_J = 125^{\circ}C$	I _R *	Тур 	Max 0.5 100	mA mA
Maximum Rate of Voltage Change (at Rated V _R)	dv/dt	10,000		V/uS
Maximum Thermal Resistance JC (per leg) Package = TO-220AB, TO-262, & TO-263	R⊕ _{JC}	2		°C/W

NOTE: Dice are available for customer applications.

Operating and Storage Junction Temperature

Package = ITO-220

 T_J

-65 to +150

οС

^{*} Pulse width < 300 uS, Duty cycle < 2%



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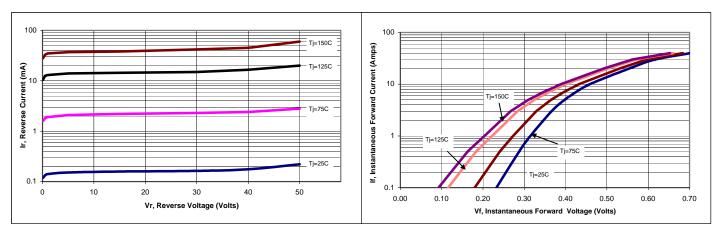


Figure 1: Typical Reverse Current

Figure 2: Typical Forward Voltage

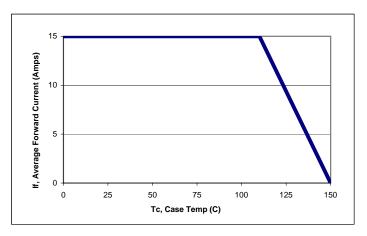


Figure 3: Current Derating, Case

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1 Lagoon Drive, Suite 410, Redwood City, CA 94065, USA Ph: 650 508 8896 FAX: 650 508 8865 Homepage: www.apdsemi.com email: info@apdsemi.com